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ABSTRACT

A non-single-crystalline semiconductor material and a device utilizing the material, the material being of an intrinsic or substantially intrinsic conductivity type and including silicon and containing a dangling bond neutralizer consisting of hydrogen and/or a halogen wherein the concentration of carbon contained in the semiconductor material is less than 4×10^{18} and the concentration of boron contained in the semiconductor material is not higher than 2×10^{17} atoms/cm³.